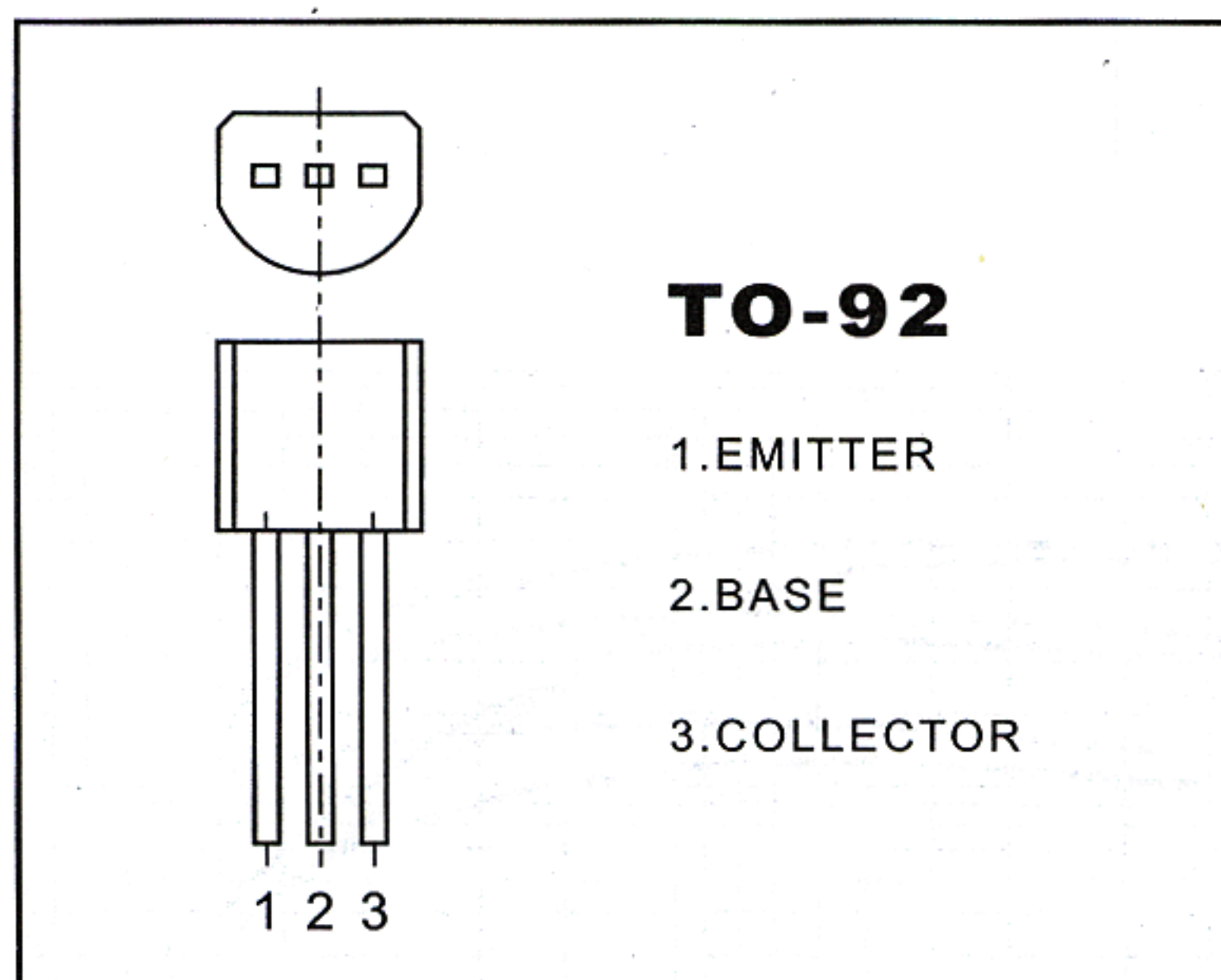


TO-92 Plastic-Encapsulate Transistors

MPS2222A TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 75 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

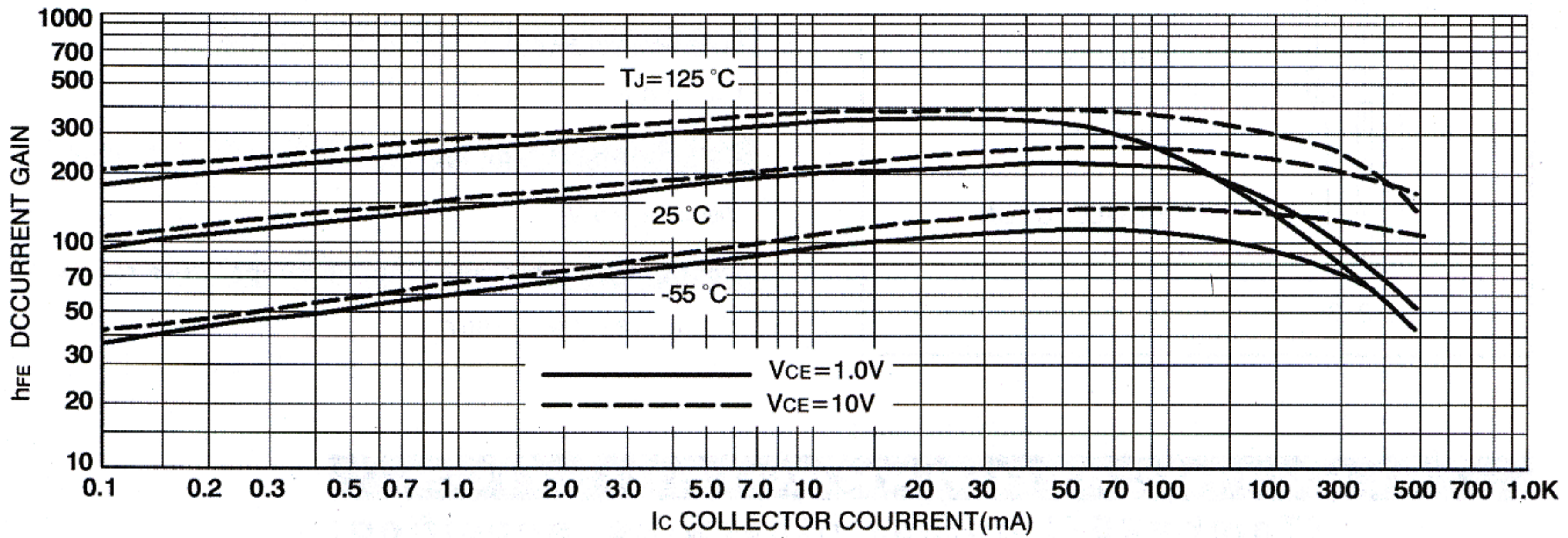
ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

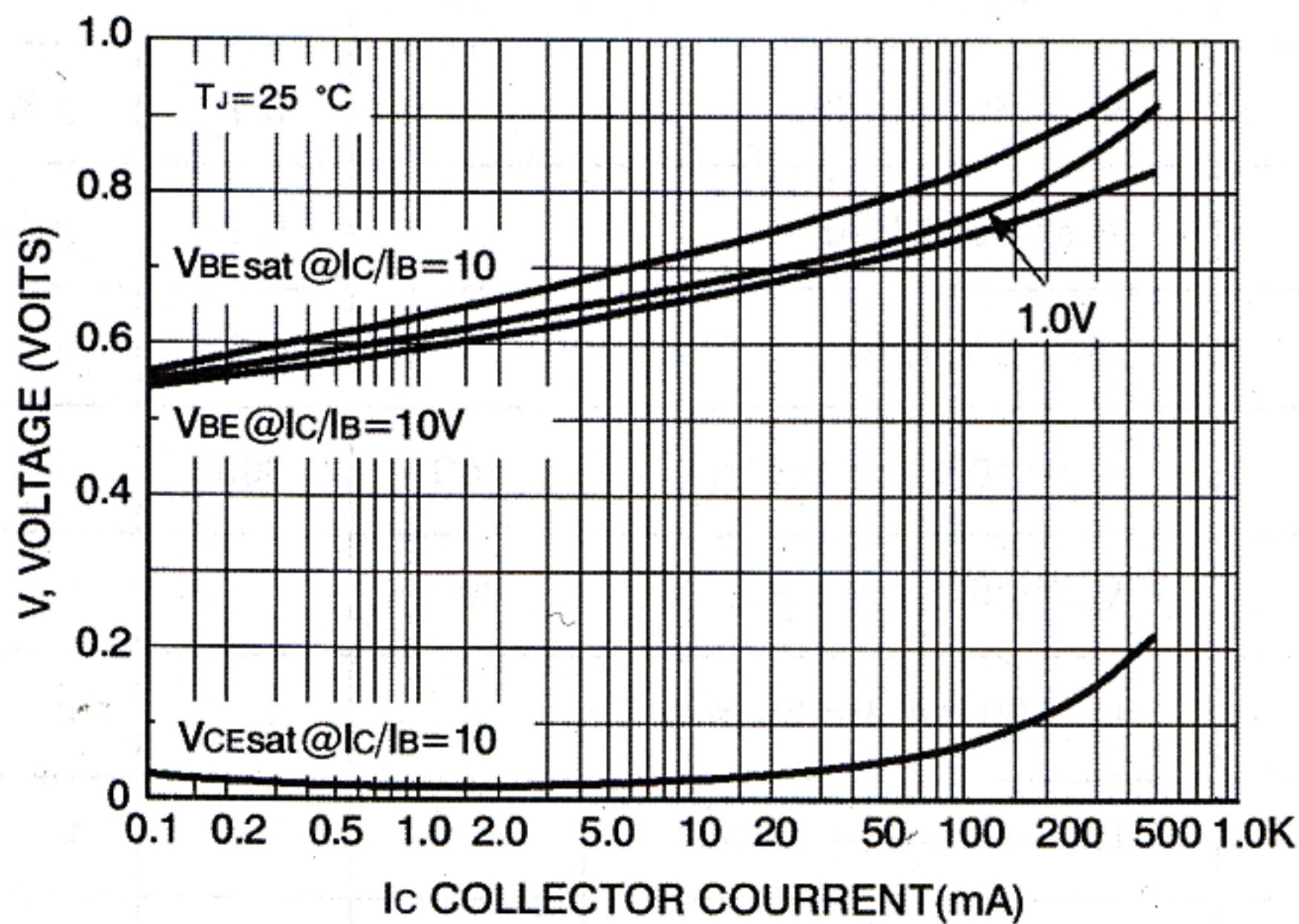
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10 \mu A, I_E = 0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10 \mu A, I_C = 0$	6.5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 70 V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 35 V, I_B = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 V, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10 V, I_C = 150 mA$	100	300	
	$h_{FE(2)}$	$V_{CE} = 10 V, I_C = 1 mA$	60		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 500 mA, I_B = 50 mA$		1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 500 mA, I_B = 50 mA$		2	V
Transition frequency	f_T	$V_{CE} = 20 V, I_C = 20 mA$ $f = 100 MHz$	300		MHz

CLASSIFICATION OF $h_{FE(1)}$

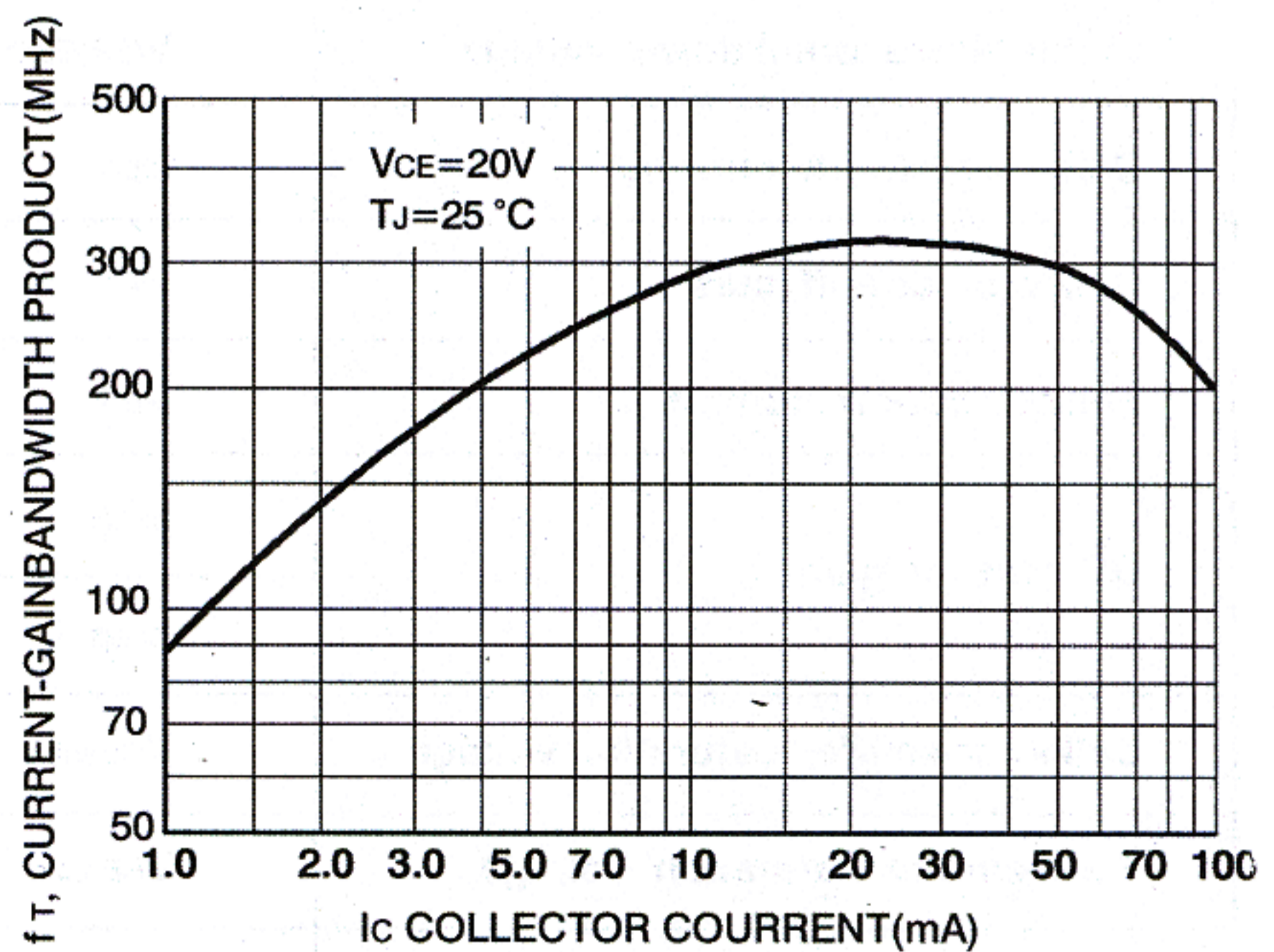
Rank	L	H
Range	100-200	200-300



DC Current Gain



"On" Volages



Current-Gain Bandwidth Product